

ABSTRACT OF THE DISCLOSURE

A voltage of a front channel 42 (gate side wiring) of a thin film transistor is made equal to a voltage of a back channel 44 (liquid crystal alignment side) thereof by electrically connecting a gate electrode 2 and a back channel electrode 82 through a gate contact hole 10 to a semiconductor layer 4 constituting the thin film transistor. The thin film transistor is fabricated through four patterning steps by simultaneously etching the semiconductor layer and a transparent electrode by using a photo resist on the front channel.

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